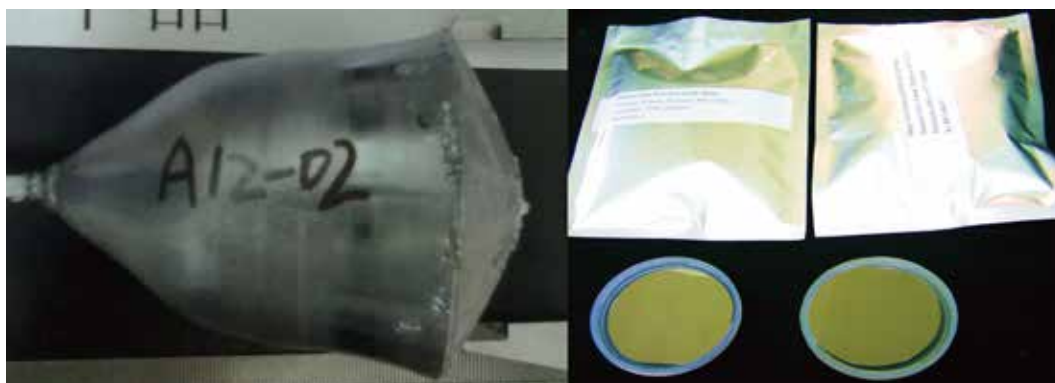


InAs-Indium Arsenide



Electrical and Dopant Specifications				
Dopant	Type	Carrier concentration (cm ⁻³)	Mobility (cm ² V ⁻¹ s ⁻¹)	E.P.D (cm ⁻²)
Undoped	n-type	$\leq 5 \times 10^{16}$	$\geq 2 \times 10^4$	≤ 50000
Sn-InP	n-type	$(5-20) \times 10^{17}$	> 2000	≤ 50000
S-InP	n-type	$(3-80) \times 10^{18}$	> 2000	≤ 50000
Zn-InP	p-type	$(3-80) \times 10^{18}$	60~300	≤ 50000

InAs Wafer Specifications		
Size	2"	3"
Diameter(mm)	50.5±0.5	76.2±0.5
Thickness(um)	500±25	600±25
Orientation	(100)/(111) ±0.5°	
Major Flat Length(mm)	16±2	22±2
Minor Flat length(mm)	8±1	11±1
TTV(um)	<10	<10
Bow(um)	<10	<10
Warp(um)	<15	<15